

ABSTRACT

Provided is a fabrication method of a semiconductor integrated circuit device which comprises forming a pushing mechanism by forming, over the upper surface of a thin film probe, a reinforcing material having a linear expansion coefficient (thermal expansion coefficient) almost equal to that of a wafer to be tested; forming a groove in the reinforcing material above a contact terminal, placing an elastomer in the groove so that a predetermined amount exceeds the groove, and disposing a pusher and another elastomer to sandwich the pusher between the elastomers. The present invention makes it possible to improve the throughput of wafer-level electrical testing of a semiconductor integrated circuit.